Ref #	Hits	Search Query	DBs	Default Operato r	Plural s	Time Stamp
S49	1	10/810779	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 15:28
S50	3250	(insulat\$3 dielectric oxide) with (high near4 constant) same (trench opening groove hole via recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 17:45
S51	1278	S50 and (insulat\$3 dielectric oxide) with (high near4 constant) same (substrate)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 15:31
S52	255	S51 and (nanometer 'nm' angstrom micrometer) with (trench opening groove hole via recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 15:40
S53	19	S51 and (dot quantum quantum near3 dot anti adj dot) with (trench opening groove hole via recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 15:47
S54	33	S51 and (dot quantum quantum near3 dot anti adj dot island) with (trench opening groove hole via recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/10/20 09:53
S55	38	S51 and (dot quantum quantum near3 dot anti adj dot island cluster) with (trench opening groove hole via recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/10/20 10:45
S56	197	S51 and (nano\$7)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 15:44
S58	24	S51 and (nano-\$10)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 15:52
S59	197	S58 or S56	US-PGPU B; USPAT; EPO; JPO	OR .	ON	2005/11/02 16:02
S61	1007	(insulat\$3 dielectric oxide) with (high near4 constant) with (trench opening groove hole via recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 17:28

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S62	1	S61 and (nano-\$10) with (trench opening groove hole via recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 17:29
S63	. 5	S61 and (quantum) with (trench opening groove hole via recess)	US-PGPU B; USPAT; EPO; JPO	OR .	ON	2005/11/02 17:38
S64	143	S61 and (nanometer nm ansgtrom "u.m"") with (trench opening groove hole via recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 17:39
S65	0	S61 and ( "'u.m'") with (trench opening groove hole via recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 17:39
S66	143	S61 and (nanometer nm ansgtrom) with (trench opening groove hole via recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 17:39
S67	5	(insulat\$3 dielectric oxide) with (high near4 constant) same (trench opening groove hole via recess) same quantum	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/02 17:48
S68	1	10/784593	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/07 08:41
S69	6	"6737364" .	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/07 08:44
S70	280135	transistor with (source drain gate channel)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/07 08:47
S71	78287	S70 and gate with (insulat\$3 dielectric)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/07 08:48
S72	71001	S70 and gate near5 (insulat\$3 dielectric)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/07 08:48
S73	1400	S70 and gate near5 (insulat\$3 dielectric) with (high near4 constant)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/07 08:49
S74	192	S73 and nano\$10 with (insulat\$3 dielectric high near4 constant)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/07 11:02

S75	4	S74 and nano\$10 with (organic)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/07 14:17
S76	3390	(organic near5 transistor "OTFT")	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/07 12:10
S77	130	(organic near5 transistor "OTFT") with nano\$10	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/07 12:10
S79	4	"6780766"	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/06/22 10:50
S80	1	"6511896".PN.	USPAT; USOCR	OR	OFF	2006/06/22 10:48
S81	1	"6399438".PN.	USPAT; USOCR	OR	OFF	2006/06/22 10:49
S82	1	"6235572".PN.	USPAT; USOCR	OR	OFF	2006/06/22 10:49
S83	1	"6200893".PN.	USPAT; USOCR	OR	OFF	2006/06/22 10:50
S84	1	"6117725".PN.	USPAT; USOCR	OR	OFF	2006/06/22 10:50
S85	1	"5893734".PN.	USPAT; USOCR	OR	OFF	2006/06/22 10:50
S86	1	"4450041".PN.	USPAT; USOCR	OR	OFF	2006/06/22 10:50
S87	30	("20010028872" "4450041" "5 292673" "5486488" "5581091 " "5641702" "5726083" "5893 734" "5958367" "6117725" "6 200893" "6231744" "6235572 " "6399438" "6511896").PN.	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/06/22 12:55
S88	1	"5475341".PN.	USPAT; USOCR	OR	OFF	2006/06/22 11:42
S89	1	"5420746".PN.	USPAT; USOCR	OR	OFF	2006/06/22 11:42

S90	1	"4472533".PN.	USPAT; USOCR	OR	OFF	2006/06/22 11:42
S91	1	"5747180".PN.	USPAT; USOCR	OR	OFF	2006/06/22 12:22
S92	1	"5470636".PN.	USPAT; USOCR	OR	OFF	2006/06/22 12:28
S93	231	(anodicoxide anodic near3 oxide) with ((oxide pentoxide) near3 tantalum)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/06/22 12:35
S94	357	((pore\$3 porous) with oxide) with ((oxide pentoxide) near3 tantalum)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/10/20 10:37
S95		((pore\$3 porous) with oxide) with ((oxide pentoxide) near3 tantalum) with (quantum nano\$5)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/06/22 12:38
S96	5	((pore\$3 porous) with oxide) with ((oxide pentoxide pen adj oxide) near3 tantalum) with (quantum nano\$5)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/06/22 12:39
S97	23686	((oxide pentoxide pen adj oxide) near3 tantalum "Ta2O5")	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/06/22 12:40

S98	21	( "Ta2O5") with (pore porous)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 12:41
S99	. 21	("Ta2O5") with ((pore porous) (nano near3 (hole wire)) nanohole nanowir\$3)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 12:44
S10 0	21	("Ta2O5" tantanum near3 oxide tantanum near3 pentoxide tantanum and pen near3 oxide) with ((pore porous) (nano near3 (hole wire)) nanohole nanowir\$3)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 12:46
S10 1	1	"5475341".PN.	USPAT; USOCR	OR	OFF	2006/06/22 12:52
S10 2	1	"5420746".PN.	USPAT; USOCR	OR	OFF	2006/06/22 12:53
S10 3	1	"5420746".PN.	USPAT; USOCR	OR	OFF	2006/06/22 12:53
S10 4	1	"5420746".PN.	USPAT; USOCR	OR	OFF	2006/06/22 12:54
S10 5	1	"4472533".PN.	USPAT; USOCR	OR	OFF	2006/06/22 12:54
S10 6	14038	(nanowire (nano near3 (structure wire pore hole tube elemnet porous dot)) nano\$8) with oxide	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/06/22 13:00

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S10 7	11	(nanowire (nano near3 (structure wire pore hole tube elemnet porous dot)) nano\$8) with ("Ta2O5" tantanum near3 oxide tantanum near3 pentoxide tantanum and pen near3 oxide)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/06/22 13:04
S10 8		(nanowire nantube nanostructure nanodot nanoelement (nano near3 (structure wire pore hole tube element porous dot)) nano\$8) with ("Ta2O5" tantanum near3 oxide tantanum near3 pentoxide tantanum and pen near3 oxide)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/06/22 13:05
S10 9	14118	(nanowire nantube nanostructure nanodot nanoelement (nano near3 (structure wire pore hole tube element porous dot)) nano\$8) with (oxide)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/06/22 13:06
S11 0	1	"5108812".PN.	USPAT; USOCR	OR	OFF	2006/06/22 13:09
S11	1	"5082709".PN.	USPAT; USOCR	OR	OFF	2006/06/22 13:11
S11 2	1	"5047274".PN.	USPAT; USOCR	OR	OFF	2006/06/22 13:11
S11 3	1	"4761330".PN.	USPAT; USOCR	OR	OFF	2006/06/22 13:11
S11 4	. 1	"4681669".PN.	USPAT; USOCR	OR	OFF	2006/06/22 13:13
S11 5	1	"5093173".PN.	USPAT; USOCR	OR	OFF	2006/06/22 13:15
S11 6	14038	(nano\$8) with (oxide)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR .	OFF	2006/06/22 13:17

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S11 7	303	(nano\$8) with (oxide) same quantum	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/06/22 13:17
S11 8	0	S117 and (nano\$8) with (oxide) with tantanum	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/06/22 13:18
S11 9	0	S117 and (nano\$8) with (oxide near3 tantanum)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR .	OFF	2006/06/22 13:19
S12 0	0	S106 and (nano\$8) with (oxide near3 tantanum)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/06/22 13:19
S12 1	155	S106 and (nano\$8) with (oxide near3 tantalum)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/06/22 13:19
S12 2	155	S106 and (nano\$8) with (oxide near3 tantalum)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/06/22 13:20
S12 3	1	"5747180".PN.	USPAT; USOCR	OR	OFF	2006/06/22 13:20

S-12	1	"5470626" DNI	LICDATE	OD	OFF	2006/06/22
4	1	"5470636".PN.	USPAT; USOCR	OR	OFF	2006/06/22 13:21
S12 5	1	"5202290".PN.	USPAT; USOCR	OR	OFF	2006/06/22 13:21
S12 6	1	"5074971".PN.	USPAT; USOCR	OR	OFF	2006/06/22 13:23
S12 7	1	"4968389".PN.	USPAT; USOCR	OR	OFF	2006/06/22 13:27
S12 8	1	"4904349".PN.	USPAT; USOCR	OR	OFF	2006/06/22 13:27
S12 9	. 1	"4563397".PN.	USPAT; USOCR	OR	OFF	2006/06/22 13:29
S13 0	1	"4277809".PN.	USPAT; USOCR	OR	OFF	2006/06/22 13:30
S13	1	"4925736".PN.	USPAT; USOCR	OR	OFF	2006/06/22 13:31
S13 2	1	"5330612".PN.	USPAT; USOCR	OR	OFF	2006/06/22 13:31
S13 3	. 1	"5202290".PN.	USPAT; USOCR	OR	OFF	2006/06/22 13:33
S13 4	1	"3945893".PN.	USPAT; USOCR	OR	OFF	2006/06/22 13:33
S13 5	1	"5470636".PN.	USPAT; USOCR	OR	OFF	2006/06/22 13:33
S13 6	1	"5202290".PN.	USPAT; USOCR	OR	OFF	2006/06/22 13:33
S13 7	1	"5074971".PN.	USPAT; USOCR	OR	OFF	2006/06/22 13:33
S13 8	1	"4968389".PN.	USPAT; USOCR	OR	OFF	2006/06/22 13:33
S13 9	1	"4925736".PN.	USPAT; USOCR	OR	OFF	2006/06/22 13:35
S14 0	1	"4904349".PN.	USPAT; USOCR	OR	OFF	2006/06/22 13:35
S14 1	1	"4650708".PN.	USPAT; USOCR	OR	OFF	2006/06/22 13:35

S14 2	170	(nano\$8) with ((oxide pentoxide) near3 tantalum)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/06/22 13:46
S14 3	. 10	(quantum) with ((oxide pentoxide) near3 tantalum)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR .	OFF	2006/06/22 13:48
S14 4	10	(quantum) with ((oxide pentoxide pen adj oxide) near3 tantalum)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/06/22 13:48
S14 5	436	(nanowire nanotube nano\$8) same ((oxide pentoxide pen adj oxide) near3 tantalum)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/06/22 13:49
S14 6	7	(nanowire nanotube nano\$8) same ((oxide pentoxide pen adj oxide) near3 tantalum) same (pore)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 13:53
S14 7	121	((oxide pentoxide pen adj oxide) near3 tantalum "Ta2O5") with (pore)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 13:54

S14 8	1069	((oxide pentoxide pen adj oxide) near3 tantalum "Ta2O5") with (pore porous hole wire wiring nano)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 13:55
S14 9	0	((oxide pentoxide pen adj oxide) near3 tantalum "Ta2O5") with (pore porous hole wire wiring nano opening) same quantum	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 13:55
S15 0	1193	((oxide pentoxide pen adj oxide) near3 tantalum "Ta2O5") with (pore porous hole wire wiring nano opening)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 13:58
S15 1	202	((oxide pentoxide pen adj oxide) near3 tantalum "Ta2O5") with (nanotube nanowire nano\$8)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 13:59
S15 2	35	((oxide pentoxide pen adjoxide) near3 tantalum "Ta2O5") with (nanotube nanowire nano\$8) and quantum	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 14:39
S15 3	60	((oxide pentoxide pen adj oxide) near3 tantalum "Ta2O5") with ("Al2O3" aluminum near3 oxide) with (nanotube nanowire nano\$8)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 14:42

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S15 4	3,	((oxide pentoxide pen adj oxide) near3 tantalum "Ta2O5") with ("Al2O3" aluminum near3 oxide) with (nanotube nanowire)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 14:44
S15 5	99	((oxide pentoxide pen adj oxide) near3 tantalum "Ta2O5") with ("Al2O3" aluminum near3 oxide) with (pore porous opening hole via )	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 15:06
S15 6	126	(((oxide pentoxide pen adj oxide) near3 tantalum) "Ta2O5") same ("Al2O3" aluminum near3 oxide) with (pore porous opening hole via)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 15:10
S15 7		(((oxide pentoxide pen adj oxide) near3 tantalum) "Ta2O5") same ("Al2O3" aluminum near3 oxide) with (qunatum)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22
S15 8	9	(((oxide pentoxide pen adj oxide) near3 tantalum) "Ta2O5") same ("Al2O3" aluminum near3 oxide) with (quantum)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 15:13
S15 9	60	(((oxide pentoxide pen adj oxide) near3 tantalum) "Ta2O5") with ("Al2O3" aluminum near3 oxide) with (trench hole opening)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 15:27

S16 0	415	(((oxide pentoxide pen adjoxide) near3 tantalum) "Ta2O5") with ("Al2O3" aluminum near3 oxide) same (trench hole opening via groove recess)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 16:29
S16 1	75	(((oxide pentoxide pen adj oxide) near3 tantalum) "Ta2O5") with ("Al2O3" aluminum near3 oxide) same (interconnect\$3)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 15:28
S16 2	21	S160 and S161	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 15:28
S16 4	4415	438/618-622.ccls.	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/06/22 16:13
S16 5	6	S160 and S164	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 16:14
S16 6	30	(((oxide pentoxide pen adj oxide) near3 tantalum) "Ta2O5") with ("Al2O3" aluminum near3 oxide) and S164	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 16:17

S16 7	1129	(((oxide pentoxide pen adj oxide) near3 tantalum) "Ta2O5") with (trench hole opening via groove recess wire wiring)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 16:30
S16 8	6	(((oxide pentoxide pen adjoxide) near3 tantalum) "Ta2O5") with (trench hole opening via groove recess wire wiring) with nano\$8	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 16:31
S16 9	13	(high near3 constant near3 dielectric) with (trench hole opening via groove recess wire wiring) same nano\$8	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/22 16:32
S17 0	14	"5907183"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/06/25 07:34
S17	1	"5600166".PN.	USPAT; USOCR	OR	OFF	2006/06/25 07:51
S17 2	1	"5470771".PN.	USPAT; USOCR	OR	OFF	2006/06/25 07:51
S17 3	1	"5460992".PN.	USPAT; USOCR	OR	OFF	2006/06/25 07:52
S17 4	1	"5445981".PN.	USPAT; USOCR	OR	OFF	2006/06/25 07:52
S17 5	1	"5304829".PN.	USPAT; USOCR	OR	OFF	2006/06/25 07:52
S17 6	6169	("ta.sub.2o.sub.5")	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR .	ON	2006/06/26 16:32

S17 7	9413	("ta.sub.2 o.sub.5")	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/26 16:32
S17 8	15552	("ta.sub.2 o.sub.5") ("ta.sub. 2o.sub.5")	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/26 16:32
S17 9	15808	(("ta.sub.2 o.sub.5") ("ta.sub. 2o.sub.5") ta205)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR .	ON	2006/06/26 16:33
S18 0	118410	(("ta.sub.2 o.sub.5") ("ta.sub. 2o.sub.5") ta205 tantalum near3 oxide tantalum near3pentoxide tatanlum pent adj oxide)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/26 16:34
S18 1	6681	(("ta.sub.2 o.sub.5") ("ta.sub. 2o.sub.5") ta205 tantalum near3 oxide tantalum near3pentoxide tatanlum pent adj oxide) with (hole pore porous via trench groove)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/26 16:35
S18 2	583	(("ta.sub.2 o.sub.5") ("ta.sub. 2o.sub.5") ta205 tantalum near3 oxide tantalum near3pentoxide tatanlum pent adj oxide) with (hole pore porous via trench groove) with (etch\$3 pattern\$3)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/26 16:38

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S18 3		(("ta.sub.2 o.sub.5") ("ta.sub. 2o.sub.5") ta205 tantalum near3 oxide tantalum near3pentoxide tatanlum pent adj oxide) with (hole pore porous via trench groove) with (etch\$3 pattern\$3) with quantum	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/26 16:36
S18 4	6	(("ta.sub.2 o.sub.5") ("ta.sub. 2o.sub.5") ta205 tantalum near3 oxide tantalum near3pentoxide tatanlum pent adj oxide) with (hole pore porous via trench groove) with (etch\$3 pattern\$3) with nano\$8	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/26 16:37
S18 5	140	(("ta.sub.2 o.sub.5") ("ta.sub. 2o:sub.5") ta205 tantalum near3 oxide tantalum near3pentoxide tatanlum pent adj oxide) near4 (hole pore porous via trench groove) with (etch\$3 pattern\$3)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/26 16:40
S18 6	40	(("ta.sub.2 o.sub.5") ("ta.sub. 2o.sub.5") ta205 (tantalum near3 oxide) (tantalum near3 pentoxide) tatanlum near3 pent adj oxide) near4 (hole pore porous via trench groove) with (etch\$3 pattern\$3)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON .	2006/06/26 16:48
S18 7	0	((("ta.sub.2 o.sub.5") ("ta.sub. 2o.sub.5") ta205 (tantalum near3 oxide) (tantalum near3 pentoxide) tatanlum near3 pent adj oxide) same ("Al2O3" aluminum near3 oxide)) near4 (hole pore porous via trench groove) with (etch\$3 pattern\$3)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/26 16:49

			,			
S18 8	5415	((("ta.sub.2 o.sub.5") ("ta.sub. 2o.sub.5") ta205 (tantalum near3 oxide) (tantalum near3 pentoxide) tatanlum near3 pent adj oxide) same ("Al2O3" aluminum near3 oxide))	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/26 16:49
S18 9	15	((("ta.sub.2 o.sub.5") ("ta.sub. 2o.sub.5") ta205 (tantalum near3 oxide) (tantalum near3 pentoxide) tatanlum near3 pent adj oxide) same ("Al2O3" aluminum near3 oxide)) with (via)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/26 16:49
S19 0	37	((("ta.sub.2 o.sub.5") ("ta.sub. 2o.sub.5") ta205 (tantalum near3 oxide) (tantalum near3 pentoxide) tatanlum near3 pent adj oxide) same ("Al2O3" aluminum near3 oxide)) with (via hole)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/26 16:50
S19 1	47	((("ta.sub.2 o.sub.5") ("ta.sub. 2o.sub.5") ta205 (tantalum near3 oxide) (tantalum near3 pentoxide) tatanlum near3 pent adj oxide) same ("Al2O3" aluminum near3 oxide)) with (via hole opening)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/26 16:50
S19 2	52	((("ta.sub.2 o.sub.5") ("ta.sub. 2o.sub.5") ta205 (tantalum near3 oxide) (tantalum near3 pentoxide) tatanlum near3 pent adj oxide) same ("Al2O3" aluminum near3 oxide)) with (via hole opening pore)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/26 16:50
S19 3	91	((("ta.sub.2 o.sub.5") ("ta.sub. 2o.sub.5") ta205 (tantalum near3 oxide) (tantalum near3 pentoxide) tatanlum near3 pent adj oxide) same ("Al2O3" aluminum near3 oxide)) with (via hole opening pore porous)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/26 16:50

S19 4	113	((("ta.sub.2 o.sub.5") ("ta.sub. 2o.sub.5") ta205 (tantalum near3 oxide) (tantalum near3 pentoxide) tatanlum near3 pent adj oxide) same ("Al2O3" aluminum near3 oxide)) with (via hole opening pore porous trench)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/26 16:50
S19 5	114	((("ta.sub.2 o.sub.5") ("ta.sub. 2o.sub.5") ta205 (tantalum near3 oxide) (tantalum near3 pentoxide) tatanlum near3 pent adj oxide) same ("Al2O3" aluminum near3 oxide)) with (via hole opening pore porous trench groove)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/26 16:51
S19 6	118	((("ta.sub.2 o.sub.5") ("ta.sub. 2o.sub.5") ta205 (tantalum near3 oxide) (tantalum near3 pentoxide) tatanlum near3 pent adj oxide) same ("Al2O3" aluminum near3 oxide)) with (via hole opening pore porous trench groove damascene)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/27 06:26
S19 7	60	((("ta.sub.2 o.sub.5") ("ta.sub. 2o.sub.5") ta205 (tantalum near3 oxide) (tantalum near3 pentoxide) tatanlum near3 pent adj oxide) same ("Al2O3" aluminum near3 oxide)) with (NANO\$8)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/27 06:35
S19 8	6	((("ta.sub.2 o.sub.5") ("ta.sub. 2o.sub.5") ta205 (tantalum near3 oxide) (tantalum near3 pentoxide) tatanlum near3 pent adj oxide) same ("Al2O3" aluminum near3 oxide)) with (PORE)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/27 06:40
S19 9	83	(high near3 dielectric with constant) with (PORE)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR,	ON	2006/06/27 06:47

S20 0	1116	(tungsten) with (PORE)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/27 06:47
S20 1	11	(tungsten) with (PORE) with nano\$8	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/27 06:47
S20 2		(tungsten) with (PORE) with nano-\$8	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/27 06:49
S20 3	4	(tungsten) with (PORE) with nano-\$9	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/27 06:57
\$20 4	,	(tungsten) with (PORE stud) with nano-\$9	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/27 06:57
S20 5	19	(tungsten) with (PORE stud wire wiring) with nano-\$9	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/27 07:25

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\$20 6	91	(tungsten) with (wire wiring) with (nano\$9 nano-\$9)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/27 07:55
\$20 7	1728	(tungsten) with (nano\$9 nano-\$9)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/27 07:55
\$20 8	35	(tungsten "W") with pore with (nano\$9 nano-\$9)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/27 07:56
S20 9	11	(tungsten) with pore with (nano\$9 nano-\$9)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/27 08:01
S21 0	49	(tungsten) with interconnect\$3 with (nano\$9 nano-\$9)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/27 08:23
S21 1	1	10/810779	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/27 08:40

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S21 2	0	(titanium with tungsten) with metal with suitable	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/27 08:42
S21 3	36005	(titanium with tungsten) with metal	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/27 08:42
S21 4	1	(titanium with tungsten) with metal with interchang\$3	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/27 08:43
S21 5	100	(titanium with tungsten) with metal with equivalent	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/27 08:44
S21 6	11	(titanium with tungsten) near4 metal with equivalent	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/27 08:49
S21 7	13	((gold silver platinum) with tungsten) near4 metal with equivalent	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/27 08:55

S21 8	0	2005/0014326	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN	OR	ON	2006/06/27 08:55
S21 9	2	"20050014326"	T; IBM_TDB US-PGPU B; USPAT; USOCR;	OR	ON	2006/06/27 09:06
			EPO; JPO; DERWEN T; IBM_TDB			
S22 0	34	"5581091"	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/27 10:07
S22 1	8	"5581091" and tungsten .	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/27 09:08
S22 2	8	S220 and tungsten	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR .	ON	2006/06/27 09:08
S22 3	9	"6709379"	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/27 10:52
S22 4	1	"6506437".PN.	USPAT; USOCR	OR	OFF	2006/06/27 10:30

S22   5	1	"6379381".PN.	USPAT; USOCR	OR	OFF	2006/06/27 10:31
S22 6	1	"6322819".PN.	USPAT; USOCR	OR	OFF	2006/06/27 10:32
S22 7	. 1	"6322588".PN.	USPAT; USOCR	OR	OFF	2006/06/27 10:32
S22 8	1	"6287628".PN.	USPAT; USOCR	OR	OFF	2006/06/27 10:34
S22 9	1	"6253443".PN.	USPAT; USOCR	OR	OFF	2006/06/27 10:35
S23 0	1	"6253443".PN.	USPAT; USOCR	OR	OFF	2006/06/27 10:35
S23	1	"5716400".PN.	USPAT; USOCR	OR	OFF	2006/06/27 10:35
S23 2	1	"5769883".PN.	USPAT; USOCR	OR	OFF	2006/06/27 10:35
S23 3	1	"5464438".PN.	USPAT; USOCR	OR	OFF	2006/06/27 10:36
S23 4	9	(tantalum adj oxide with aluminum adj oxide) with equivalent	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/06/27 10:53
S23 6	2	"20050255315"	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/10/20 09:41
S23 7	. 1	09/830895	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/10/20 09:43

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1	10/810779	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/10/20 09:44
1810	(((oxide pentoxide pen adj oxide) near3 tantalum) "Ta2O5" "TaO") with (pore porous opening hole via groove recess)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/20 11:24
73	S239 and (dot quantum quantum near3 dot anti adj dot island) with (trench pore porous opening groove hole via recess)	US-PGPU B; USPAT; EPO; JPO	OR .	ON	2006/10/20 09:53
708	((pore\$3 porous hole trench opening recess hole) with oxide) with ((oxide pentoxide) near3 tantalum "Ta2O5" "TaO")	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/10/20 10:40
. 22	((pore\$3 porous hole trench opening recess hole) with oxide) with ((oxide pentoxide) near3 tantalum "Ta2O5" "TaO") with (silicon semiconductor) near3 (substrate wafer)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/10/20 10:41
3694	(insulat\$3 dielectric oxide) with (high near4 constant) same (trench opening groove hole via recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/10/20 10:45
. 1503	S243 and (insulat\$3 dielectric oxide) with (high near4 constant) same (substrate)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/10/20 10:45
	S244 and (dot quantum quantum near3 dot anti adj dot island cluster) with (trench opening groove hole via recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/10/20 11:25
	73 708 22	oxide) near3 tantalum) "Ta2O5" "TaO") with (pore porous opening hole via groove recess)  73 S239 and (dot quantum quantum near3 dot anti adj dot island) with (trench pore porous opening groove hole via recess)  708 ((pore\$3 porous hole trench opening recess hole) with oxide) with ((oxide pentoxide) near3 tantalum "Ta2O5" "TaO")  22 ((pore\$3 porous hole trench opening recess hole) with oxide) with ((oxide pentoxide) near3 tantalum "Ta2O5" "TaO") with (silicon semiconductor) near3 (substrate wafer)  3694 (insulat\$3 dielectric oxide) with (high near4 constant) same (trench opening groove hole via recess)  1503 S243 and (insulat\$3 dielectric oxide) with (high near4 constant) same (substrate)  48 S244 and (dot quantum quantum near3 dot anti adj dot island cluster) with (trench opening groove hole via	B; USPAT; USOCR; EPO; IPO; DERWEN T; IBM_TDB   US-PGPU B; USPAT; USOCR; EPO; IPO; DERWEN T; IBM_TDB   US-PGPU USOCR; EPO; JPO; DERWEN T; IBM_TDB   US-PGPU B; US-PG	1810 (((oxide pentoxide pen adjoxide) near3 tantalum) "Ta2O5" "TaO") with (pore porous opening hole via groove recess)  73 S239 and (dot quantum quantum near3 dot anti adjot island) with (trench pore porous opening groove hole via recess)  708 ((pore\$3 porous hole trench opening recess hole) with oxide) with ((oxide pentoxide) near3 tantalum "Ta2O5" "TaO")  22 ((pore\$3 porous hole trench opening recess hole) with oxide) with ((oxide pentoxide) near3 tantalum "Ta2O5" "TaO")  22 ((pore\$3 porous hole trench opening recess hole) with oxide) with ((oxide pentoxide) near3 tantalum "Ta2O5" "TaO") with (silicon semiconductor) near3 (substrate wafer)  3694 (insulat\$3 dielectric oxide) with (high near4 constant) same (trench opening groove hole via recess)  1503 S243 and (insulat\$3 dielectric oxide) with (high near4 constant) same (substrate)  48 S244 and (dot quantum quantum near3 dot anti adj dot island cluster) with (trench opening groove hole via  48 S244 and (dot quantum quantum near3 dot anti adj dot island cluster) with (trench opening groove hole via	B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB   US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB   US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB   US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB   US-PGPU B; USPAT; EPO; JPO DERWEN T; IBM_TDB   US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB   US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB   US-PGPU B; US-PG

624	24	G245 17 33	110 5055	0.5	1000	
S24 6	34	S245 and (silicon semiconductor) near3 (wafer substrate)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/10/20 11:23
S24 7	8	"6709379"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/10/20 10:51
S24 8	19	("3952334"   "3987219"   "4323055"   "4818572"   "5464438"   "5478237"   "5716400"   "5769883"   "5843172"   "6206915"   "6210436"   "6240616"   "6253443"   "6273908"   "6287628"   "6322588"   "6322819"   "6379381"   "6506437").PN.	US-PGPU B; USPAT; USOCR	OR	OFF	2006/10/20 10:51
S24 9	4574	438/618-622.ccls.	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/10/20 11:23
S25 0	3398	S249 and (silicon semiconductor) near3 (wafer substrate)	US-PGPU B; USPAT; EPO; JPO	OR ·	ON	2006/10/20 11:23
S25 1	20	S250 and (((oxide pentoxide pen adj oxide) near3 tantalum) "Ta2O5" "TaO") with (pore porous opening hole via groove recess cavity)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/20 11:30
S25 2	2	S251 and (dot quantum quantum near3 dot anti adj dot island cluster) with (pore pourous trench opening groove hole via recess cavity)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2006/10/20 11:26
S25 3		09/827759	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/20 11:35

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S25	0	(semiconductor adj substrate)	US-PGPU	OR	ON	2006/10/20
4		with crystalline with	B; USPAT;			11:38
		ellectrical with insulative and	USOCR;			
		opening and quantum adj dots	EPO; JPO;			
		and (tantalum adj oxide	DERWEN			
		"Ta2O5").clm.	T;			
			IBM_TDB			